

1. 产品特点 Product features

- 不含卤素Halogens free
(Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm)
- 电流转换率(Current transfer ratio)
CTR: 50~600% at IF =5mA, VCE =5V
- 输入与输出高隔离电压(Viso=3750 V rms)
High isolation voltage between inputs and output (Viso=3750 V rms)
- 紧凑型4引脚SOP,外形尺寸为2.0mm
Compact 4 Pin SOP with a 2.0 mm profile
- 符合欧盟REACH法规
Compliance with EU REACH
- 无Pb且符合ROHS标准
Pb free and RoHS compliant

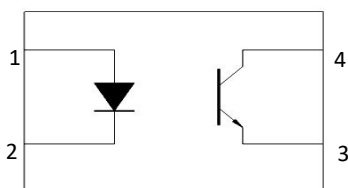
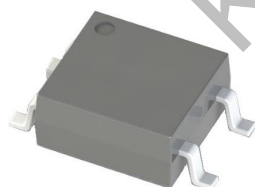
2. 产品描述 Product Description

- KTP357系列包含一个红外发射二极管,光耦合到一个光电晶体管构成光电耦合器
KTP357 series contains an infrared emitting diode, optically coupled to a phototransistor detector.
- 采用4引脚小外形SMD封装的器件
The devices in a 4-pin small outline SMD package

3. 产品应用 Product Applications

- 直流转换器 DC Converters
- 可编程控制器 Programmable controllers
- 电信设备 Telecommunication equipments
- 不同电位和阻抗电路间的信号传输
Signal transmission between circuits of different potentials and impedances

4. 功能图 Functional Diagram



引脚配置 Pin Configuration

1. 阳极Anode
2. 阴极Cathode
3. 发射极Emitter
4. 集电极Collector

5. 光电特性 Electrical-Optical characteristics

• 最大限度额定值(温度=25±5℃) Absolute Maximum Ratings(Ta=25℃)

参数 Parameter		符号 Symbol	额定值 Rated Value	单位 Unit
输入 Input	正向电流 Forward current	I_F	50	mA
	峰值正向电流(1us脉冲) Peak forward current (1us pulse)	I_{FP}	1	A
	反向电压 Reverse voltage	V_R	6	V
	输入功耗 Input Power dissipation	P_D	70	mW
	降额因子(约 Ta=100℃) Derating factor (about Ta=100℃)		2.9	mW/°C
输出 Output	集电极电流 Collector current	I_C	50	mA
	集电极与发射极间电压 Collector and emitter Voltage	V_{CEO}	80	V
	发射极与集电极间电压 Emitter and Collector Voltage	V_{ECO}	7	V
	输出功耗 Output Power dissipation	P_C	150	mW
	降额因子(高于Ta=70℃) Derating factor (above Ta = 70℃)		3.7	mW/°C
总消耗功率 Total Consume Power		P_{TOT}	200	mW
隔离电压 (1*) Isolation Voltage		V_{iso}	3750	Vrms
工作温度 Operating temperature		T_{OPR}	-55 to +110	°C
储存温度 Storage temperature		T_{STG}	-55 to +125	°C
焊接温度 (2*) Soldering temperature		T_{SOL}	260	°C

附注(Notes):

1* 交流电源1分钟内, 相对湿度40~60%环境下, 隔离电压测试方法, 引脚1&2短接在一起, 引脚3&4短接在一起
AC for 1 minute, 40~60%RH in this test, Pin 1,2 are shorted together, and 3,4 are shorted together

2* 焊接时间为10秒 Soldering time is 10 seconds

6. 电气特性(Ta=25°C,除非另有规定)

Electrical Characteristics(Ta=25°C unless specified otherwise)

参数 Parameter		符号 Symbol	最小值 Min.	规格值 Typ.	最大值 Max.	单位 Unit	条件 Condition
输入 In put	正向电压 Forward voltage	V_F	-	1.2	1.4	V	$I_F=20\text{mA}$
	反向电流 Reverse current	I_R	-	-	10	μA	$V_R=4\text{V}$
	输入电容 Input capacitance	C_{in}	-	30	250	pF	$V=0, f=1\text{kHz}$
输出 Out put	集电极与发射极间暗电流 Collector-Emitter dark current	I_{CEO}	-	-	100	nA	$V_{CE}=20\text{V}$ $I_F=0\text{mA}$
	集电极与发射极间击穿电压 Collector-Emitter breakdown voltage	V_{CEO}	80	-	-	V	$I_C=0.1\text{mA}$ $I_F=0\text{mA}$
	发射极与集电极间击穿电压 Emitter-Collector breakdown voltage	V_{ECO}	7	-	-	V	$I_E=0.01\text{mA}$ $I_F=0\text{mA}$
传输特性 Transfer Characteristics	集电极与发射极间饱和电压 Collector-Emitter saturation voltage	$V_{CE(sat)}$	-	0.1	0.2	V	$I_F=20\text{mA}$ $I_C=1\text{mA}$
	电流传输比 Current transfer ratio	CTR	50	-	600	%	$I_F=5\text{mA}$ $V_{CE}=5\text{V}$
	隔离电阻 Isolation resistance	R_{ISO}	5×10^{10}	-	-	Ω	$V_{IO}=500\text{Vdc}$ 40~60% R.H.
	浮动电容 Floating capacitance	C_f	-	0.6	1.0	pF	$V_{IO}=0, f=1\text{MHz}$
	上升时间 Rise time	t_r	-	3	18	μs	$V_{CE}=2\text{V},$ $I_C=2\text{mA},$ $R_L=100\Omega$
	下降时间 Fall time	t_f	-	4	18	μs	

- 传输特性等级表($T_a=25^{\circ}\text{C}$, 除非另有规定)

Transfer Characteristics level table ($T_a=25^{\circ}\text{C}$ unless specified otherwise)

参数 Parameter		符号 Symbol	最小值 Min.	规格值 Typ.	最大值 Max.	单位 Unit	条件 Condition
电流传输比 Current Transferratio	KTP357	CTR	50	-	600	%	$I_F=5\text{mA}$ $V_{CE}=5\text{V}$
	KTP357-A		80	-	160		
	KTP357-B		130	-	260		
	KTP357-C		200	-	400		
	KTP357-D		300	-	600		
	KTP357-E		100	-	200		
	KTP357-F		150	-	300		

7. 特性曲线 Characteristic Curves

图1. 正向电流与环境温度关系

Forward current vs Ambient temperature

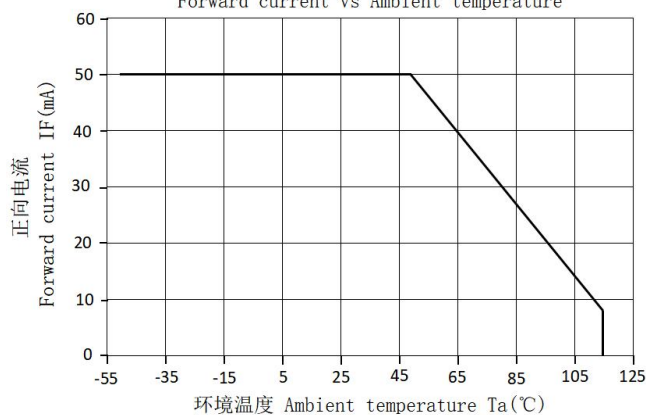


图2. 正向电流与正向电压的关系

Figure1. Forward Current VS Forward Voltage

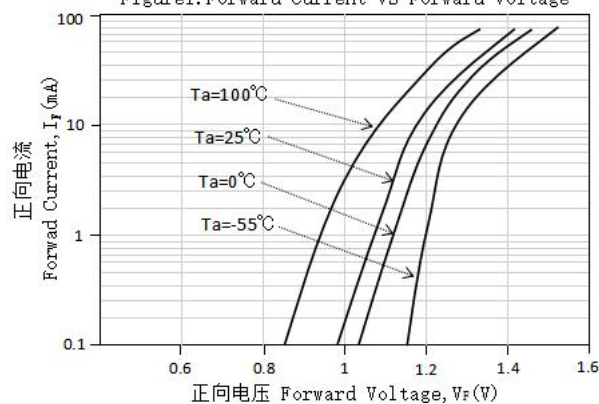


图3. 电流传输比与正向电流

Current Transfer Ratio vs Forward Current

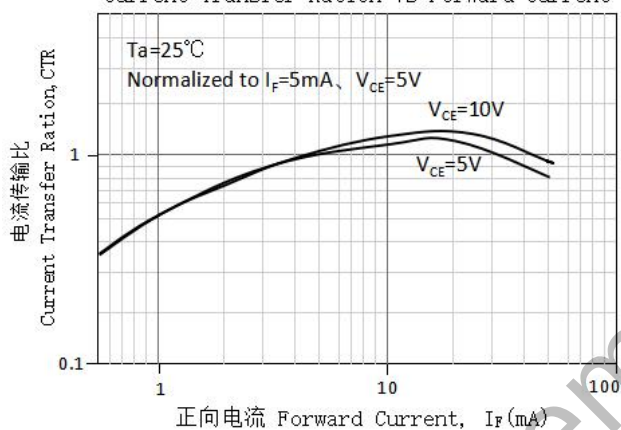


图4. 集电极电流与集电极-发射极电压

Collector Current vs Collector-Emitter Voltage

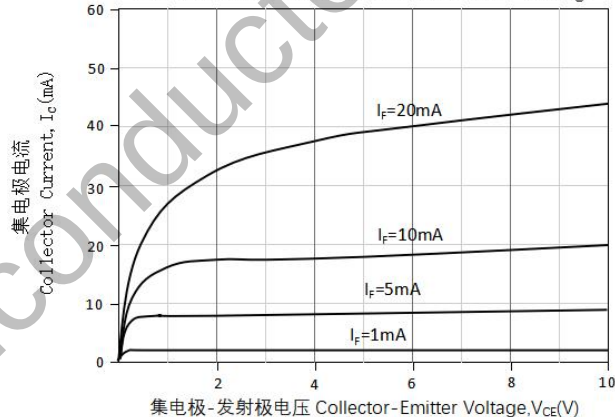


图5. 集电极电流与环境温度关系

Collector Current vs Ambient Temperature

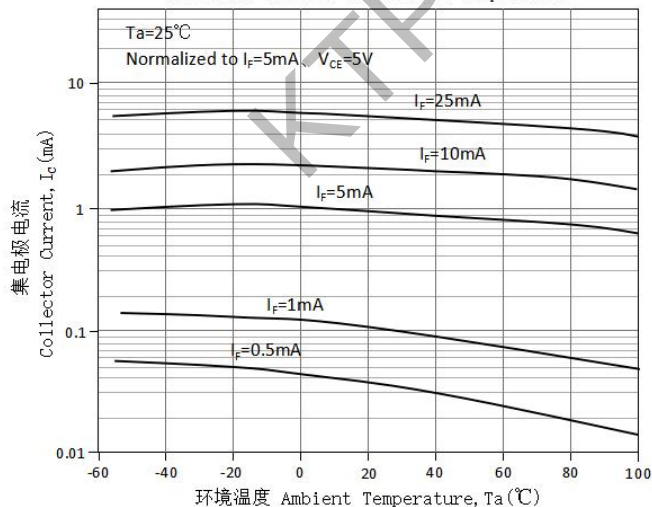


图6. 集电极暗电流与环境温度的关系

Collector Dark Current vs Ambient Temperature

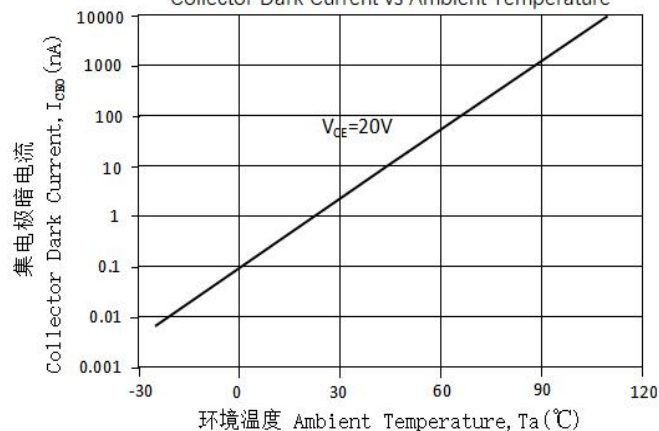


图7. 集电极-发射极饱和电压与环境温度关系
Collector-Emitter Saturation Voltage
vs Ambient Temperature

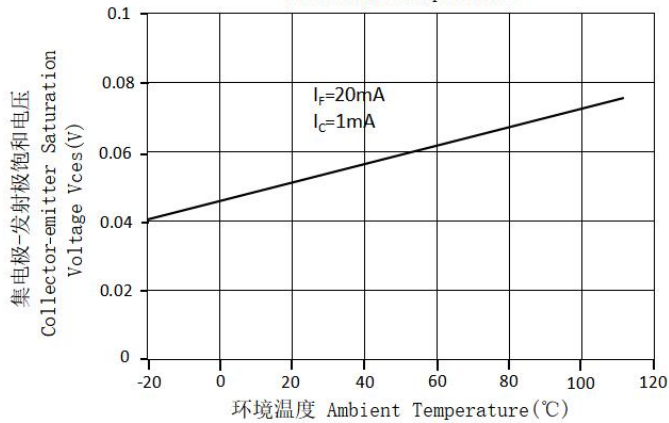


图8. 开关时间与负载电阻的关系
Switching Time vs Load Resistance

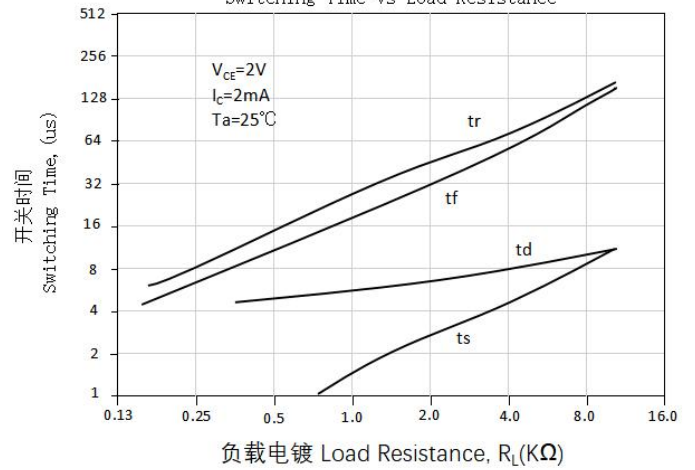
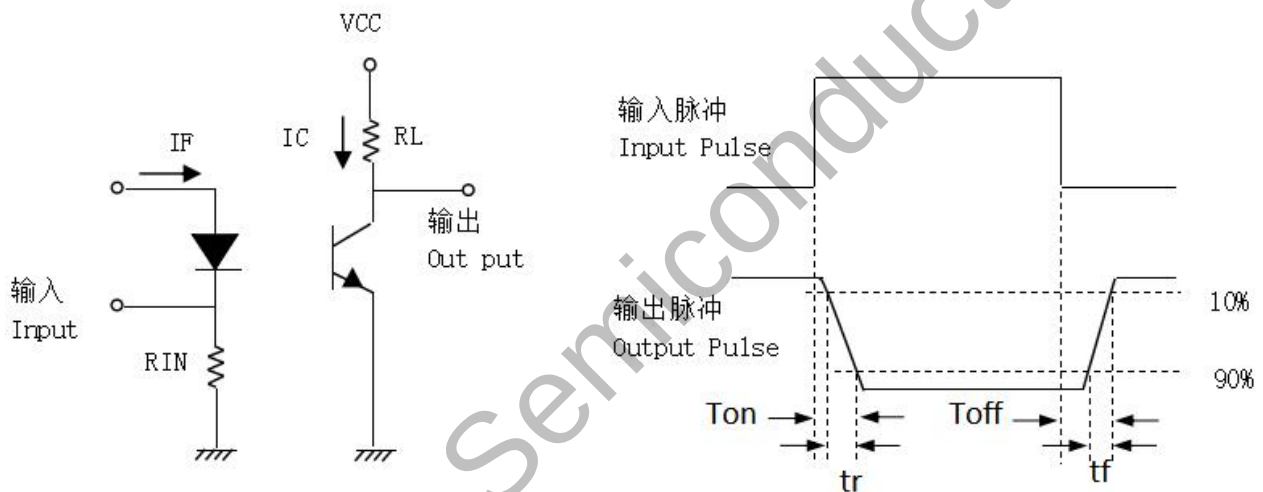


图9. 开关时间测试电路与波形
Switching Time Test Circuit vs Waveforms



8. 订单信息 Order Information

- 零件编号 Part Number

KTP357-X-Y-F-AW-W

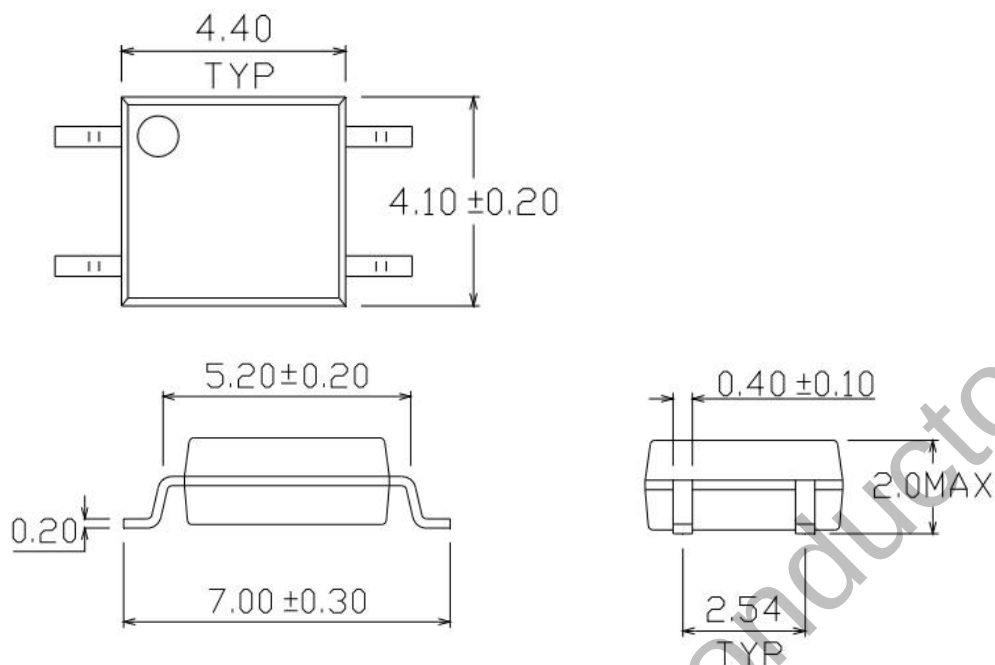
附注(Notes):

- X = 表示CTR等级(A、B、C、D、E、F 或 无)
CTR Rank (A, B, C, D, E, F or none)
- Y = 载带和卷轴包装方式(TA)
Tape and reel option (TA)
- F = 表示支架框架选项(F:铁、无:铜) Lead frame option (F: Iron, None: copper)
- AW = 表示消费级 Consumer-grade
- W = 表示内部标识码(有或无)Indicates internal identification code (with or without)

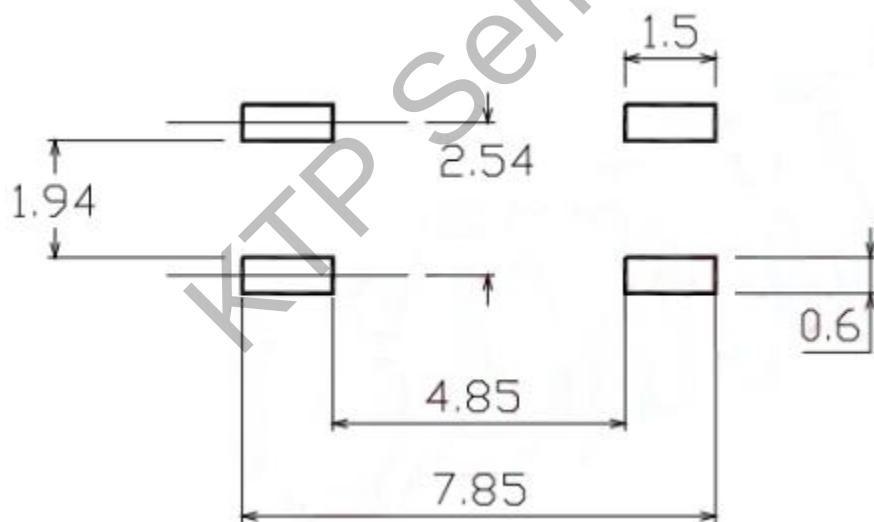
9. 封装尺寸(单位:毫米) Package Drawing(Unit:mm)

- 包装尺寸 (尺寸单位为mm)

Package Dimension (Dimensions in mm)



- 表面贴片类型PIN脚焊盘布局 Surface patch type PIN foot pad layout

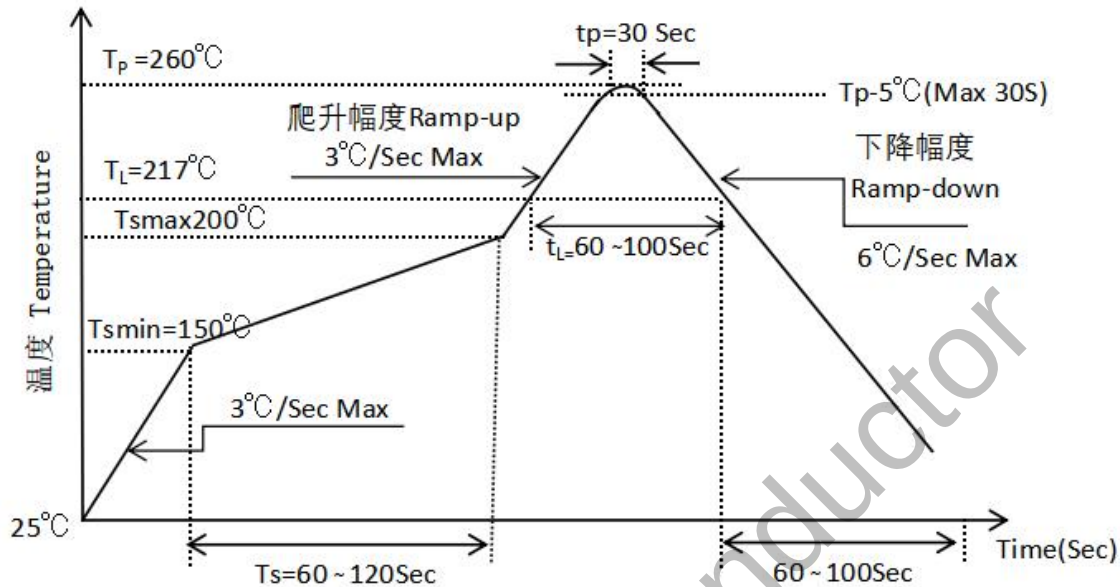


10. 焊接温度曲线 Temperature Profile Of Soldering

• 回流焊温度曲线 Reflow soldering

建议在下面所示的温度和时间分布条件下, 进行一次回流焊作业, 不得超过三次

One time soldering reflow is recommended within the condition of temperature and time profile shown below. Do not solder more than three times.



项目 Item	符号 Symbol	最小值 Min.	最大值 Max.	单位 Unit
预热温度 Preheat Temperature	T_s	150	200	°C
预热时间 Preheat Time	t_s	60	120	s
升温速率 Ramp-Up Rate (T_L to T_p)	-	-	3	°C/s
液相线温度 Liquidus Temperature	T_L	217		°C
高于液相线温度(T_L)的时间 Time above Liquidus Temperature T_L	t_L	60	100	s
峰值温度 Peak Temperature	T_p	-	260	°C
T_c 在(T_p-5)和 T_p 之间的时间 Time During Which T_c Is Between (T_p-5) and T_p	t_p	-	30	s
降温速率 Ramp-down Rate(T_p to T_L)	-	-	6	°C/s